

ABSTRACT OF THE DISCLOSURE

The invention provides a method of manufacturing a thin film transistor capable of reducing the induced photo-electric current and thus improving the quality of the liquid crystal display, and reducing the number of required photo 5 masks saving on the cost of fabrication. A stack structure is formed first, by successively depositing a gate electrode, a first insulation layer, a semiconductor layer, an ohmic contact layer, and a photoresist layer. Subsequently, a second insulation layer is deposited on the substrate, and the photoresist layer and the second insulation layer on the photoresist layer 10 are removed in a lift-off process. Last, a source electrode, a drain electrode, a passivation layer, and a transparent electrode layer, are formed to complete the thin film transistor process.

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